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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/602,915	06/25/2003	Kazuhiko Yamamoto	60188-606	1774
75	90 03/24/2006		EXAMINER	
Jack Q. Lever, Jr. McDERMOTT, WILL & EMERY 600 Thirteenth Street, N.W. Washington, DC 20005-3096			NADAV, ORI	
			ART UNIT	PAPER NUMBER
			2811	
			DATE MAILED: 03/24/2006	6 ·

Please find below and/or attached an Office communication concerning this application or proceeding.

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Office Action Summary		Application No.	Applicant(s)	7			
		10/602,915	YAMAMOTO, KAZUHIKO				
		Examiner	Art Unit				
		Ori Nadav	2811				
Period fo	The MAILING DATE of this communication a or Reply	ppears on the cover sheet v	vith the correspondence address				
WHI(- Exte after - If NO - Failu Any	ORTENED STATUTORY PERIOD FOR REP CHEVER IS LONGER, FROM THE MAILING nsions of time may be available under the provisions of 37 CFR of SIX (6) MONTHS from the mailing date of this communication. O period for reply is specified above, the maximum statutory period are to reply within the set or extended period for reply will, by stative to reply within the set or extended period for reply will, by stative to reply extended by the Office later than three months after the mailed patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUN 1.136(a). In no event, however, may a od will apply and will expire SIX (6) MO ute, cause the application to become A	ICATION. I reply be timely filed INTHS from the mailing date of this communication ABANDONED (35 U.S.C. § 133).				
Status							
1)⊠	Responsive to communication(s) filed on 12	April 2005.					
2a)□	☐ This action is FINAL . 2b) ☐ This action is non-final.						
3)	3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is						
	closed in accordance with the practice under	r <i>Ex parte Quayle</i> , 1935 C.	D. 11, 453 O.G. 213.				
Disposit	ion of Claims						
4)⊠	Claim(s) 1,3,4 and 21 is/are pending in the a	application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.						
5)[Claim(s) is/are allowed.						
· ·	Claim(s) 1,3,4 and 21 is/are rejected.						
•	Claim(s) is/are objected to.	//					
8)	Claim(s) are subject to restriction and	i/or election requirement.	,				
Applicat	ion Papers						
	The specification is objected to by the Exami						
10)	The drawing(s) filed on is/are: a) a						
	Applicant may not request that any objection to the						
	Replacement drawing sheet(s) including the corre			d).			
11)[]	The oath or declaration is objected to by the	Examiner. Note the attache	ad Office Action of John PTO-192.				
Priority	under 35 U.S.C. § 119						
-	Acknowledgment is made of a claim for foreign All b) Some * c) None of:		§ 119(a)-(d) or (f).				
	1. Certified copies of the priority docume2. Certified copies of the priority docume		Application No.				
	3. Copies of the certified copies of the process.						
	application from the International Bure		n received in this reducine. etage				
* ;	See the attached detailed Office action for a li		ot received.				
Attachmei		_					
	ce of References Cited (PTO-892) ce of Draftsperson's Patent Drawing Review (PTO-948)		y Summary (PTO-413) o(s)/Mail Date				
3) X Info	ce of Dransperson's Patent Drawing Review (P10-946) mation Disclosure Statement(s) (PTO-1449 or PTO/SB/0 er No(s)/Mail Date <u>9/16/04, 4/12/05</u> .	= 1 	f Informal Patent Application (PTO-152)				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1, 4 and 21 are rejected under 35 U.S.C. 102(e) as being anticipated by Lee et al. (6,844,604).

Lee et al. teach in figure 1C and related text a semiconductor device comprising:

a gate insulating film having a multilayer structure including a zirconium oxide film 20 (ZrO₂, column 6, lines 51-54) and a high dielectric constant film 18 which is formed of an oxide of a metal other than zirconium and substantially directly contacting the zirconium oxide film, wherein the high dielectric constant film is a hafnium oxide film, and wherein the gate insulating film includes a zirconium silicate film 12 formed under the zirconium oxide film.

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Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claim 3 is rejected under 35 U.S.C. 103(a) as being unpatentable over Lee et al. in view of Yang et al. (6,451,647).

Lee et al. teach substantially the entire claimed structure, as applied to claim 1 above, except a high dielectric constant film contains nitrogen. Yang et al. teach the high dielectric constant film (hafnium silicate layer) contains nitrogen (column 5, lines 19-23). It would have been obvious to one having ordinary skill in the art at the time the invention was made to incorporate the teaching of Yang et al. into the device taught by Senzaki in order to provide better protection to the gate by increasing the dielectric constant of the high dielectric constant film.

Response to Arguments

Applicant's arguments with respect to claims 1, 3, 4 and 21 have been considered but are most in view of the new ground(s) of rejection.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ori Nadav whose telephone number is 571-272-1660. The examiner can normally be reached between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

O.N. 3/19/06

ORI NADAV
PRIMARY EXAMINER
TECHNOLOGY CENTER 2800